A1 cont'd

This control is performed to compensate for the greater heat losses that are experienced at the perimeter of the support structure. Thus, the goal of the control is to attempt to provide a uniform substrate temperature by compensating with additional heating of the substrate near the perimeter. However, similar to U.S. Patent No. 5,977,519, this patent does not address the temperature dependence of the films, particularly organosilicate films, but merely aims to compensate for heat losses at the outside surface so as to maintain a generally even heating of the substrate.

Replace paragraph 15 on page 5 with the following:

A2

In other examples involving deposition on substrates having dimensions of 730mm x 920mm, the temperature control comprises maintaining the temperature of the perimeter area within a range of about 350°C to about 460°C, while maintaining the area inside of the perimeter area within a range of about 340°C to about 450°C, while maintaining the temperature of the perimeter area of a surface of the substrate within a range between about 10°C less than the temperature of the area of the surface inside of the perimeter area to about 20°C higher that the temperature of the area of the surface inside of the perimeter area.

Replace paragraph 24 on page 6 with the following:

A3

Figure 5 is a view of the susceptor of Figure 3 with a schematic representation of a chamber wall surrounding the susceptor.

Replace paragraph 25 on page 6 with the following:

A4

Figure 4 is a view of the susceptor of Figure 2A with a schematic representation of a chamber wall surrounding the susceptor.

Replace paragraph 30 on page 7 with the following:

A5

Where a range of values is provided, it is understood that each intervening value (to the tenth of the unit of the lower limit unless the context clearly dictates otherwise) between the upper and lower limit of that range and any other stated or intervening value in that stated range is encompassed within the invention. The upper and lower limits of these smaller ranges may independently be included in the smaller ranges also encompassed within the

A5 cont'd

invention, subject to any specifically excluded limit in the stated range. Where the stated range includes one or both of the limits, ranges excluding either or both of those included limits are also included in the invention.

Replace paragraph 44 on pages 10-11 with the following:

A6

The sealing material may be composed of substantially pure diamond powder, such as an industrial grade diamond material available from, for example, Beta Diamond Products, of Yorba Linda, Calif. The diamond powder may be composed of particles having an average particle size between about five and fifty microns. Most of the particles may have a particle size of about fifteen to thirty microns. Alternatively, the sealing material may be composed of a ceramic material such as magnesium oxide or boron nitride, for example, or of a mixture of a diamond powder and a ceramic material such as magnesium oxide or boron nitride.

Replace paragraph 52 on page 13 with the following:

A7

Figure 8, in comparison, shows the linear relationship between temperature change and deposition rates of organosilicate films using TEOS as a source material. This plot shows that, for example, an increase in susceptor temperature from about 350 °C to about 400 °C results in a decrease in the deposition rate of from about 1050 Å/min to about 900 Å/min. As can be seen, the organosilicate film deposited using TEOS as a precursor is very temperature sensitive and requires very particular attention in order to achieve substantial film uniformity in a deposited film.

IN THE CLAIMS:

A marked up version of the claims showing the amendments made herein is attached as Exhibit D. A copy of the claims that will be pending upon entry of the present amendment is attached as Exhibit E.

Please revise claims 1-7, 10 and 12 to read as follows:

A8

1. (Amended) A method of controlling thickness uniformity of a film deposited on a substrate, said method comprising the steps of:

providing a substrate in a processing chamber;

controlling a temperature of at least two distinct locations on the substrate